



FORM PTO-1449 INFORMATION DISCLOSURE STATEMENT	ATTY. DOCKET 033035 M 0341	SERIAL NO. 10/691,540
	APPLICANTS: Kensaku MOTOKI, et al.	
	FILING DATE October 24, 2003	GROUP ART UNIT 1722

U.S. PATENT DOCUMENTS

*Examiner's Initials		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB-CLASS	FILING DATE, IF APPROPRIATE
	AA						
	AB						
	AC						
	AD						
	AE						
	AF						
	AG						

FOREIGN PATENT DOCUMENTS

*Examiner's Initials		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB-CLASS	ABSTRACT TRANSLATION	
							YES	NO
/MS/	AH	97/11518	03/27/97	WO			X	
/MS/	AI	07-273048	10/20/1995	JP			X	
/MS/	AJ	11-135770	05/21/1999	JP			X	
	AK							

OTHER INFORMATION (Including Author, Title, Date, Pertinent Pages, Etc.)

/MS/	AL	Japanese Patent Office Action for corresponding Patent Application No. 2000-519462 (April 18, 2006)
/MS/	AM	H. Okumura, et al. "Epitaxial growth of cubic and hexagonal GaN on GaAs on GaAs by gas-source molecular epitaxy," Appl. Phys. Lett. 59(9), 1991.08.26, pp. 1058-1060
/MS/	AN	NANIWAE, et al., "Growth of Single Crystal GaN Substrate Using Hydride Vapor Phase Epitaxy," Journal of Crystal Growth 99, 1990, pp. 381-384
	AO	
	AP	
	AQ	

EXAMINER: /Matthew Song/	DATE CONSIDERED: 11/08/2007
*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.	